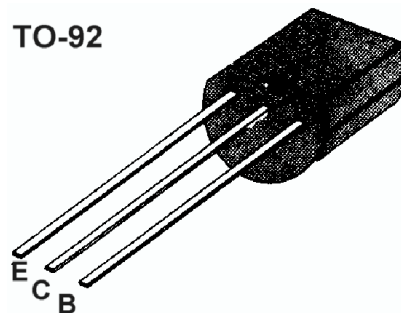


MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V <sub>CBO</sub>	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-150	mA
Collector Power Dissipation	P <sub>C</sub>	625	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55~150	°C

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ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Common Emitter DC Current Gain	h <sub>FE</sub>	70		400		V <sub>CE</sub> = -6V, I <sub>C</sub> = -2mA
Collector Cut-off Current	I <sub>CBO</sub>			-0.1	μA	V <sub>CB</sub> = -50V, I <sub>E</sub> =0
Emitter Cut-off Current	I <sub>EBO</sub>			-0.1	μA	V <sub>EB</sub> = -5V, I <sub>C</sub> =0
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-50			V	I <sub>C</sub> = -0.1mA, I <sub>E</sub> =0
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-50			V	I <sub>C</sub> = -1mA, I <sub>B</sub> =0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5			V	I <sub>E</sub> = -0.1mA, I <sub>C</sub> =0
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>		-0.1	-0.3	V	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>			-1.1	V	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA
Gain bandwidth product	f <sub>r</sub>	80			MHz	I <sub>C</sub> = -1mA, V <sub>CE</sub> = -10V
Common Base Output Capacitance	C <sub>ob</sub>		4.0	7.0	PF	V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f = 1MHz
Noise Figure	N <sub>F</sub>		1.0	10	dB	V <sub>CE</sub> = -6V, I <sub>C</sub> = -0.1mA, f=1KHz, R <sub>g</sub> =10KΩ

h<sub>FE</sub> Classification

Classification	O	Y	GR
h <sub>FE</sub>	70~140	120~240	200~400